New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

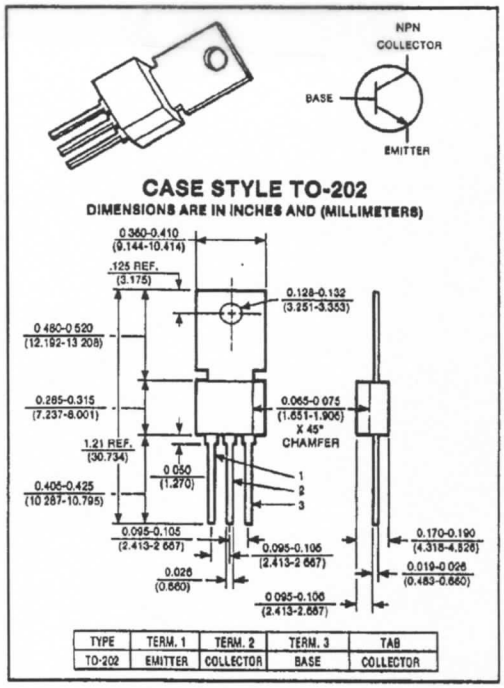
TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

NPN POWER TRANSISTORS

COMPLEMENTARY TO THE D43C SERIES

D42C Series

30-80 VOLTS
3 AMP, 12.5 WATTS



Features:

- High free-air power dissipation
- NPN complement to D43C PNP
- Low collector saturation voltage (0.5V typ. @ 3.0A I_C)
- Excellent linearity
- Fast Switching

maximum ratings (T_A = 25°C) (unless otherwise specified)

RATING	SYMBOL	D42C1, 2, 3	D42C4, 5, 6	D42C7, 8, 9	D42C10, 11, 12	UNITS
Collector-Emitter Voltage	V_{CEO}	30	45	60	80	Volts
Collector-Emitter Voltage	V_{CES}	40	55	70	90	Volts
Emitter Base Voltage	V_{EBO}	5	5	5	5	Volts
Collector Current — Continuous Peak(1)	I_C I_{CM}	3 5	3 5	3 5	3 5	A
Base Current — Continuous	I_B	2	2	2	2	A
Total Power Dissipation @ T_A = 25°C @ T_C = 25°C	P_D	2.1 12.5	2.1 12.5	2.1 12.5	2.1 12.5	Watts
Operating and Storage Junction Temperature Range	T_J,T_{stg}	-55 to +150	-55 to +150	-55 to +150	-55 to +150	°C

thermal characteristics

Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	60	60	60	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	10	10	10	10	°C/W
Maximum Lead Temperature for Soldering Purposes: ⅛" from Case for 5 Seconds	T_L	+260	+260	+260	+260	°C

(1) Pulse Test Pulse Width = 300ms Duty Cycle ≤ 2%.

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Quality Semi-Conductors

electrical characteristics (T_C = 25° C) (unless otherwise specified)

CHARACTERISTIC		SYMBOL	MIN	TYP	MAX	UNIT
off characteristics[1]						
Collector-Emitter Sustaining Voltage (I_C = 100mA)	D42C1, 2, 3 D42C4, 5, 6 D42C7, 8, 9 D42C10, 11, 12	$V_{CEO(sus)}$	30 45 60 80	— — — —	— — — —	Volts
Collector Cutoff Current (V_{CE} = Rated V_{CES})		I_{CES}	—	—	10	μA
Emitter Cutoff Current (V_{EB} = 5V)		I_{EBO}	—	—	100	μA
second breakdown						
Second Breakdown with Base Forward Biased		FBSOA	SEE FIGURES 3 & 4			
on characteristics[1]						
DC Current Gain (I_C = 200mA, V_{CE} = 1V)	D42C1, 4, 7, 10 D42C2, 5, 8, 11 D42C3, 6, 9, 12	h_{FE}	25 100 40	— — —	— 220 120	—
(I_C = 1A, V_{CE} = 1V) (I_C = 2A, V_{CE} = 1V)	D42C1, 4, 7, 10 D42C2, 5, 8, 11 D42C3, 6, 9, 12	h_{FE}	10 20 20	— — —	— — —	—
Collector-Emitter Saturation Voltage (I_C = 1A, I_B = 50mA) (I_C = 1A, I_B = 100mA)	D42C2, 5, 8, 11 D42C3, 6, 9, 12 D42C1, 4, 7, 10	$V_{CE(sat)}$ $V_{CE(sat)}$	— — —	— — —	0.5 0.5 0.5	Volts Volts
Base-Emitter Saturation Voltage (I_C = 1A, I_B = 100mA)		$V_{BE(sat)}$	—	—	1.3	Volts
dynamic characteristics						
Collector Capacitance (V_{CB} = 10V, f = 1M_{Hz})		C_{CBO}	—	—	100	pF
Current-Gain — Bandwidth Product (I_C = 20mA, V_{CE} = 4V)		f_T	—	50	—	MHz
switching characteristics						
Resistive Load						
Delay Time + Rise Time	I_C = 1A, I_{B1} = I_{B2} = 0.1A,	$t_d + t_r$	—	100	—	nS
Storage Time	V_{CC} = 30V, t_p = 25 μsec	t_s	—	500	—	
Fall Time		t_f	—	75	—	

(1) Pulse Test PW = 300ms Duty Cycle ≤ 2%.